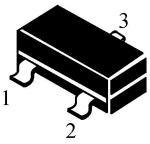
# 桂林斯壯桂微電子有限責任公司
# Guilin Strong Micro-Electronics Co.,Ltd.

GMB736

SOT—23

1. BASE
2. EMITTER
3. COLLECTOR




## ■FEATURES 特點

**PNP Low Frequency Amplifier Transistor**

## ■MAXIMUM RATINGS ($T_a$=25℃) 最大額定值

| Characteristic<br>特性參數 | Symbol<br>符號 | Rating<br>額定值 | Unit<br>單位 |
|---|---|---|---|
| Collector-Base Voltage<br>集電極-基極電壓 | $V_{CBO}$ | -60 | V |
| Collector-Emitter Voltage<br>集電極-發射極電壓 | $V_{CEO}$ | -60 | V |
| Emitter-Base Voltage<br>發射極-基極電壓 | $V_{EBO}$ | -5 | V |
| Collector Current-Continuous<br>集電極電流-連續 | Ic | -300 | mA |
| Collector Power Dissipation<br>集電極耗散功率 | $P_C$ | 200 | mW |
| Junction Temperature<br>結溫 | $T_j$ | 150 | ℃ |
| Storage Temperature Range<br>儲存溫度 | $T_{stg}$ | -55～150 | ℃ |

## ■DEVICE MARKING 打標

| GMB736(2SB736) | | | | | |
|---|---|---|---|---|---|
| MARK | BW1 | BW2 | BW3 | BW4 | BW5 |
| $H_{FE1}$ | 110~180 | 135~220 | 170~270 | 200~320 | 250~400 |

GMB736

## ■ELECTRICAL CHARACTERISTICS 電特性

($T_A$=25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

| Characteristic<br>特性參數 | Symbol<br>符號 | Test Condition<br>測試條件 | Min<br>最小值 | Typ<br>典型值 | Max<br>最大值 | Unit<br>單位 |
|---|---|---|---|---|---|---|
| Collector Cutoff Current<br>集電極截止電流 | $I_{CBO}$ | $V_{CB}$=-50V,<br>$I_E$=0 | — | — | -0.1 | μA |
| Emitter Cutoff Current<br>發射極截止電流 | $I_{EBO}$ | $V_{EB}$=-5V,<br>$I_C$=0 | — | — | -0.1 | μA |
| Collector-Base Breakdown Voltage<br>集電極-基極擊穿電壓 | $V_{(BR)CBO}$ | $I_C$=-100 μA | -60 | — | — | V |
| Collector-Emitter Breakdown Voltage<br>集電極-發射極擊穿電壓 | $V_{(BR)CEO}$ | $I_C$=-1.0mA | -60 | — | — | V |
| Emitter-Base Breakdown Voltage<br>發射極-基極擊穿電壓 | $V_{(BR)EBO}$ | $I_E$=-100 μA | -5 | — | — | V |
| DC Current Gain<br>直流電流增益 | $H_{FE1}$ | $V_{CE}$=-1V,<br>$I_C$=-50mA | 110 | 200 | 400 | — |
| DC Current Gain<br>直流電流增益 | $H_{FE2}$ | $V_{CE}$=-2V,<br>$I_C$=-300mA | 30 | — | — | — |
| Collector-Emitter Saturation Voltage<br>集電極-發射極飽和壓降 | $V_{CE(sat)}$ | $I_C$=-300mA,<br>$I_B$=-30mA | — | -0.35 | -0.6 | V |
| Base-Emitter Saturation Voltage<br>基極-發射極飽和壓降 | $V_{BE(sat)}$ | $I_C$=-300mA,<br>$I_B$=-30mA | — | — | -1.2 | V |
| Base-Emitter Saturation<br>基極-發射極電壓 | $V_{BE}$ | $V_{CE}$=-6V,<br>$I_C$=-10mA | -0.6 | -0.66 | -0.7 | V |
| Transition Frequency<br>特徵頻率 | $f_T$ | $V_{CE}$=-6V,<br>$I_C$=-10mA | — | 100 | — | MHz |
| Collector Output Capacitance<br>輸出電容 | $C_{ob}$ | $V_{CB}$=-6V,$I_E$=0,<br>f=1MHz | — | 13 | — | pF |